

THYRISTOR/ THYRISTOR

NEWADD-A-pak™ Power Modules

Features

- Electrically isolated: DBC base plate
- 3500 V_{RMS} isolating voltage
- Standard JEDEC package
- Simplified mechanical designs, rapid assembly
- Auxiliary cathode terminals for wiring convenience
- High surge capability
- Wide choice of circuit configurations
- Large creepage distances
- UL E78996 approved 

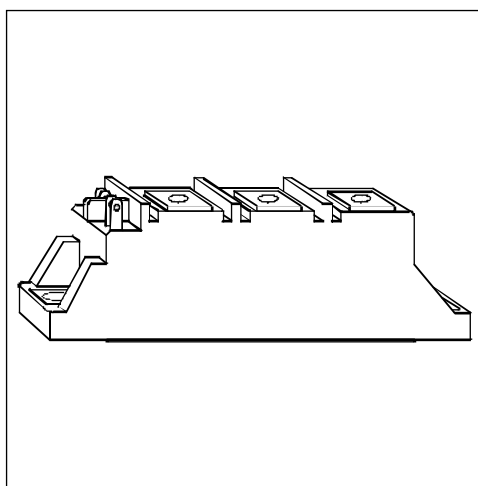
105 A

Description

These IRKU/V series of NEW ADD-A-paks use power thyristors in two circuit configurations. The semiconductor chips are electrically isolated from the base plate, allowing common heatsinks and compact assemblies to be built. They can be interconnected to form single phase bridges (IRKU+IRKV) or 6-pulse midpoint connection bridge. These modules are intended for general purpose high voltage applications such as high voltage regulated power supplies, battery charge and DC motor speed control circuits.

Major Ratings and Characteristics

Parameters	IRKU/V105	Units
$I_{T(AV)}$ @ 85°C	105	A
$I_{T(RMS)}$	165	A
I_{TSM} @ 50Hz	1785	A
@ 60Hz	1870	A
I^2t @ 50Hz	15.91	KA ² s
@ 60Hz	14.52	KA ² s
$I^2\sqrt{t}$	159.1	KA ² √s
V_{RRM} range	400 to 1600	V
T_{STG}	- 40 to 125	°C
T_J	- 40 to 130	°C



ELECTRICAL SPECIFICATIONS

Voltage Ratings

Type number	Voltage Code	V_{RRM} , maximum repetitive peak reverse voltage V	V_{RSM} , maximum non-repetitive peak reverse voltage V	V_{DRM} , max. repetitive peak off-state voltage, gate open circuit V	I_{RRM} I_{DRM} 130°C mA
IRKU/V105	04	400	500	400	20
	08	800	900	800	
	12	1200	1300	1200	
	16	1600	1700	1600	

On-state Conduction

Parameters	IRKU/V105	Units	Conditions
$I_{T(AV)}$ Max. average on-state current	105	A	180° conduction, half sine wave, $T_C = 85^\circ\text{C}$
$I_{T(RMS)}$ Max. RMS on-state current. @ T_C	165 77	°C	DC
I_{TSM} Max. peak, one cycle non-repetitive on-state current	1785 1870 1500 1570 2000 2100	A	t=10ms No voltage reappplied t=8.3ms 100% V_{RRM} reappplied t=10ms Sinusoidal half wave, Initial $T_J = T_J \text{ max.}$ t=8.3ms t=10ms $T_J = 25^\circ\text{C}$, t=8.3ms no voltage reappplied
I^2t Max. I^2t for fusing	15.91 14.52 11.25 10.27 20.00 18.30	KA ² s	t=10ms No voltage reappplied t=8.3ms 100% V_{RRM} reappplied t=10ms Initial $T_J = T_J \text{ max.}$ t=8.3ms t=10ms $T_J = 25^\circ\text{C}$, t=8.3ms no voltage reappplied
$I^2\sqrt{t}$ Max. $I^2\sqrt{t}$ for fusing (1)	159.1	KA ² /s	t=0.1 to 10ms, no voltage reappl., $T_J = T_J \text{ max.}$
$V_{T(To)}$ Max. value of threshold voltage (2)	0.80 0.85	V	Low level (3) High level (4) $T_J = T_J \text{ max.}$
r_t Max. value of on-state slope resistance (2)	2.37 2.25	mΩ	Low level (3) High level (4) $T_J = T_J \text{ max.}$
V_{TM} Max. peak on-state voltage	1.64	V	$I_{TM} = \pi \times I_{T(AV)}$ $I_{FM} = \pi \times I_{F(AV)}$ $T_J = 25^\circ\text{C}$
di/dt Max. non-repetitive rate of rise of turned on current	150	A/μs	$T_J = 25^\circ\text{C}$, from 0.67 V_{DRM} , $I_{TM} = \pi \times I_{T(AV)}$, $I_g = 500\text{mA}$, $t_r < 0.5 \mu\text{s}$, $t_p > 6 \mu\text{s}$
I_H Max. holding current	200	mA	$T_J = 25^\circ\text{C}$, anode supply = 6V, resistive load, gate open circuit
I_L Max. latching current	400		$T_J = 25^\circ\text{C}$, anode supply = 6V, resistive load

(1) I^2t for time $t_X = I^2\sqrt{t} \times \sqrt{t_X}$

(2) Average power = $V_{T(To)} \times I_{T(AV)} + r_t \times (I_{T(RMS)})^2$

(3) $16.7\% \times \pi \times I_{AV} < I < \pi \times I_{AV}$

(4) $I > \pi \times I_{AV}$

Triggering

Parameters	IRK.U/V105	Units	Conditions
P_{GM} Max. peak gate power	12	W	
$P_{G(AV)}$ Max. average gate power	3		
I_{GM} Max. peak gate current	3	A	
$-V_{GM}$ Max. peak negative gate voltage	10	V	Anode supply = 6V resistive load
V_{GT} Max. gate voltage required to trigger	4.0		
	2.5		
	1.7		
I_{GT} Max. gate current required to trigger	270	mA	Anode supply = 6V resistive load
	150		
	80		
V_{GD} Max. gate voltage that will not trigger	0.25	V	$T_J = 125^\circ\text{C}$, rated V_{DRM} applied
I_{GD} Max. gate current that will not trigger	6	mA	$T_J = 125^\circ\text{C}$, rated V_{DRM} applied

Blocking

Parameters	IRKU/V 105	Units	Conditions
I_{RRM} Max. peak reverse and I_{DRM} off-state leakage current at V_{RRM} , V_{DRM}	20	mA	$T_J = 130^\circ\text{C}$, gate open circuit
V_{INS} RMS isolation voltage	2500 (1 min) 3500 (1 sec)	V	50 Hz, circuit to base, all terminals shorted
dv/dt Max. critical rate of rise of off-state voltage (5)	500	V/ μs	$T_J = 130^\circ\text{C}$, linear to 0.67 V_{DRM} , gate open circuit

(5) Available with $dv/dt = 1000\text{V}/\mu\text{s}$, to complete code add S90 i.e. IRKU105/16S90.

Thermal and Mechanical Specifications

Parameters	IRKU/V105	Units	Conditions
T_J Junction operating temperature range	- 40 to 130	$^\circ\text{C}$	
T_{stg} Storage temperature range	- 40 to 125		
R_{thJC} Max. internal thermal resistance, junction to case	0.135	K/W	Per module, DC operation
R_{thCS} Typical thermal resistance case to heatsink	0.1		Mounting surface flat, smooth and greased. Flatness < 0.03 mm; roughness < 0.02 mm
T Mounting torque $\pm 10\%$ to heatsink busbar	5	Nm	A mounting compound is recommended and the torque should be rechecked after a period of 3 hours to allow for the spread of the compound
	3		
wt Approximate weight	83 (3)	g (oz)	
Case style	TO-240AA		JEDEC

ΔR Conduction (per Junction)

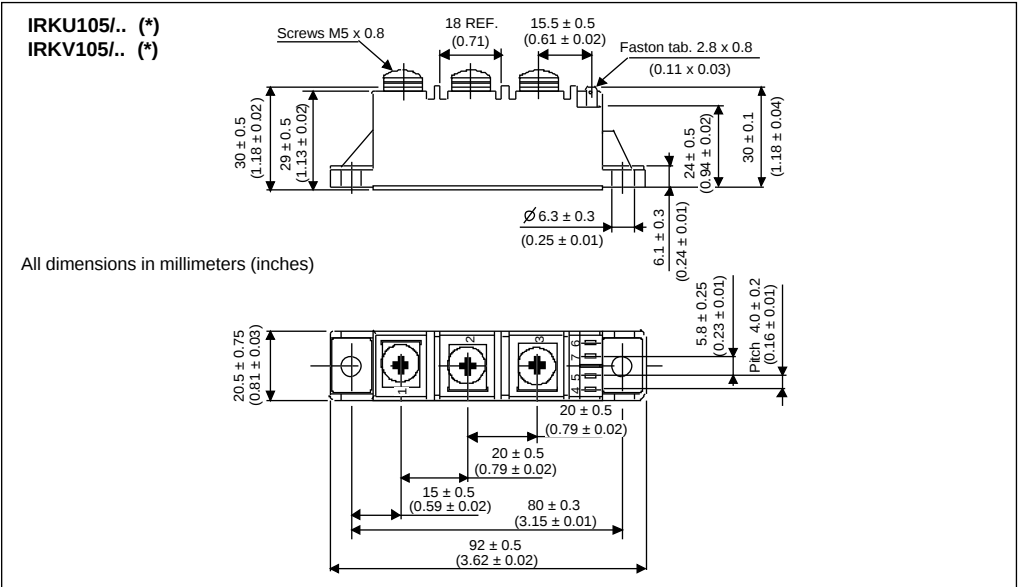
(The following table shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC)

Devices	Sine half wave conduction					Rect. wave conduction					Units
	180°	120°	90°	60°	30°	180°	120°	90°	60°	30°	
IRKU/V105	0.04	0.05	0.06	0.08	0.12	0.03	0.05	0.06	0.08	0.12	$^\circ\text{C}/\text{W}$

IRKU/V105 Series

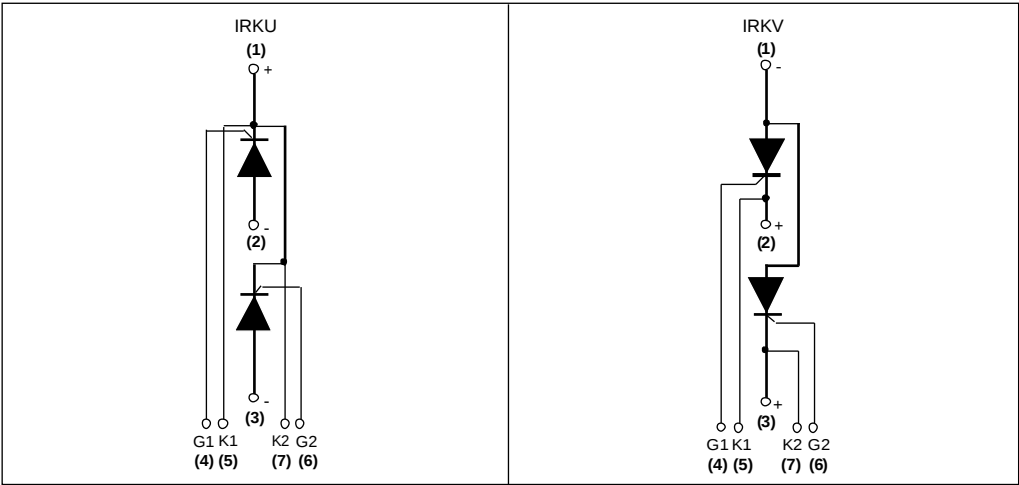
Bulletin I27136 rev. B 09/97

Outlines Table



(*) For terminals connections, see Circuit Configurations Table

Circuit Configurations Table



NOTE: To order the Optional Hardware see Bulletin I27900

Ordering Information Table

Device Code					
IRK	U	105	/	16	S90
①	②	③		④	⑤
1	- Module type				
2	- Circuit configuration (See Circuit Configuration Table)				
3	- Current code				
4	- Voltage code (See Voltage Ratings Table)				
5	- dv/dt code: S90 = dv/dt 1000 V/μs No letter = dv/dt 500 V/μs				

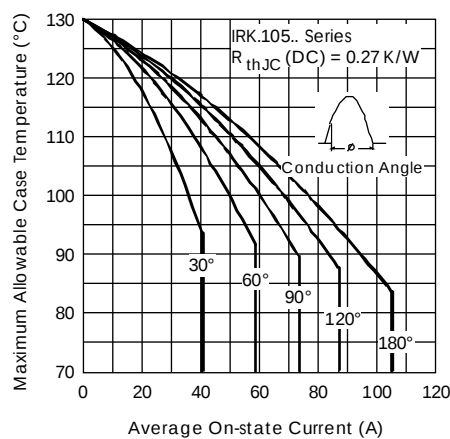


Fig. 1 - Current Ratings Characteristics

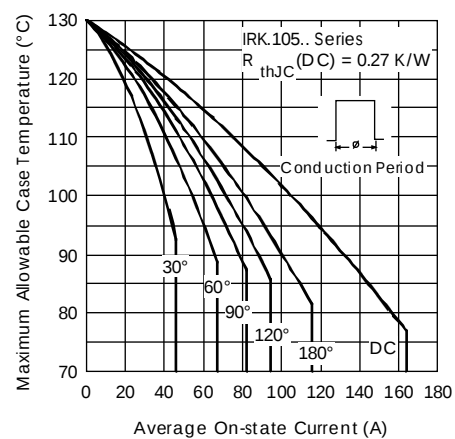


Fig. 2 - Current Ratings Characteristics

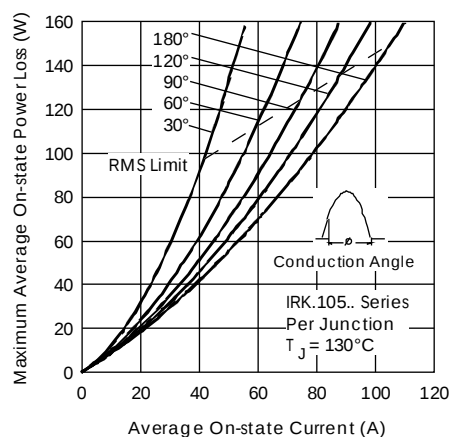


Fig. 3 - On-state Power Loss Characteristics

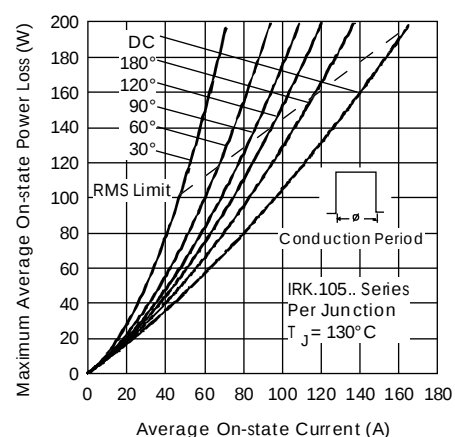


Fig. 4 - On-state Power Loss Characteristics

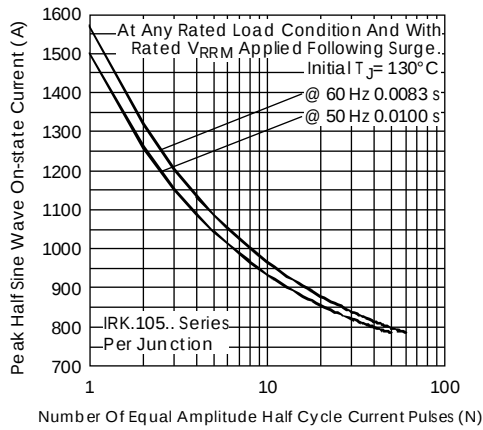


Fig. 5 - Maximum Non-Repetitive Surge Current

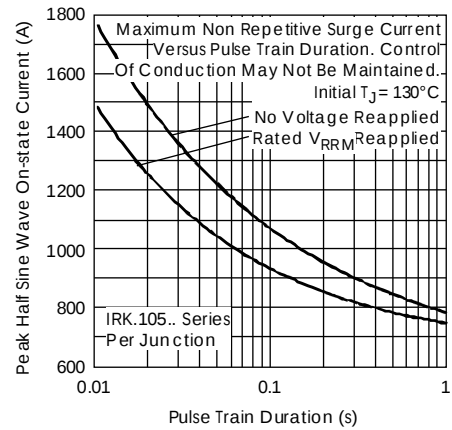


Fig. 6 - Maximum Non-Repetitive Surge Current

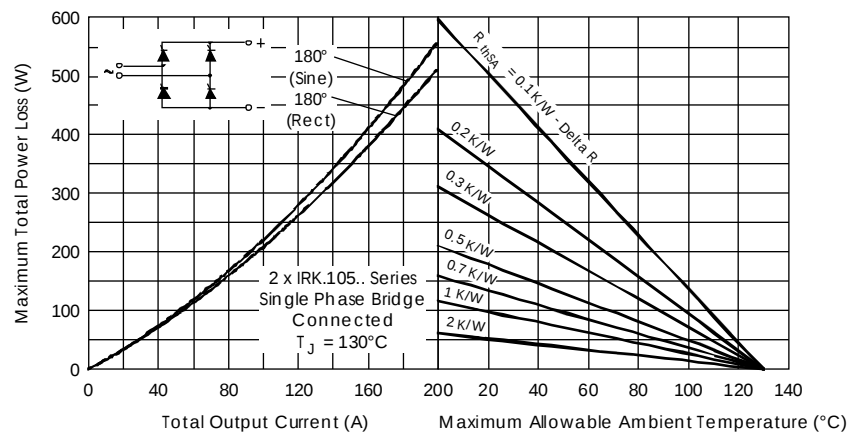


Fig. 7 - On-state Power Loss Characteristics (Single Phase Bridge IRKU+IRKV)

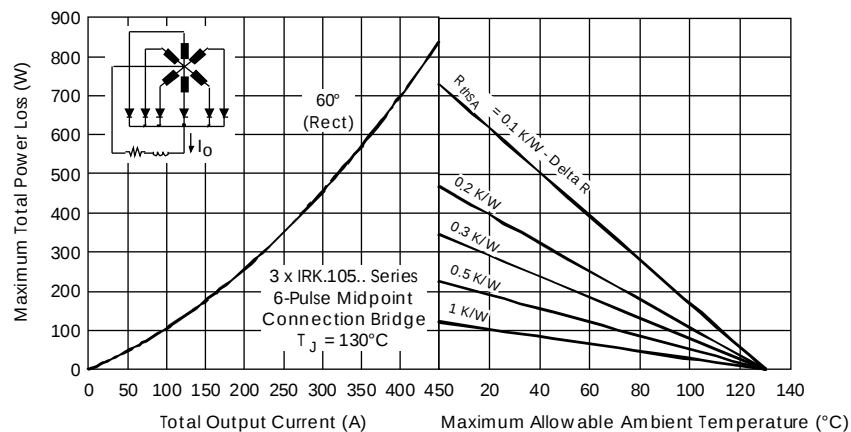


Fig. 8 - On-state Power Loss Characteristics

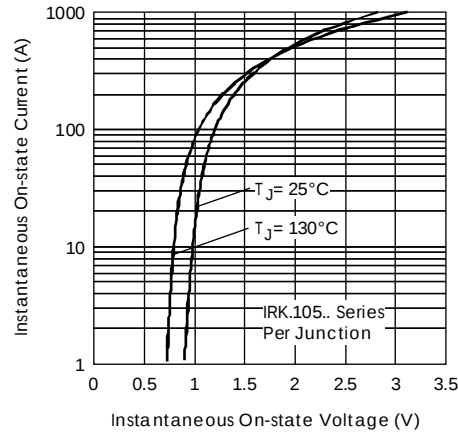


Fig. 9 - On-state Voltage Drop Characteristics

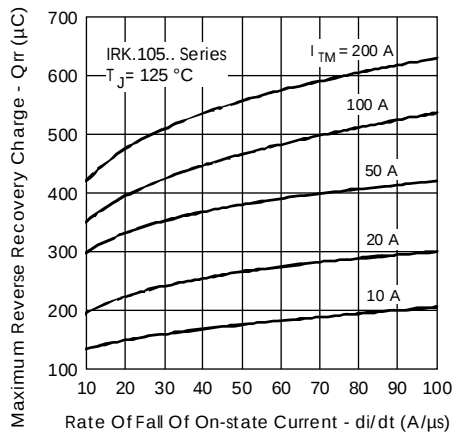


Fig. 10 - Recovery Charge Characteristics

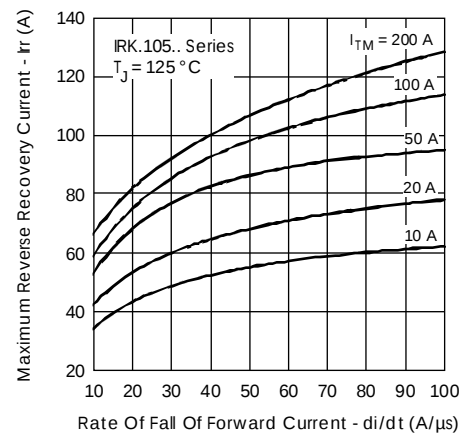


Fig. 11 - Recovery Current Characteristics

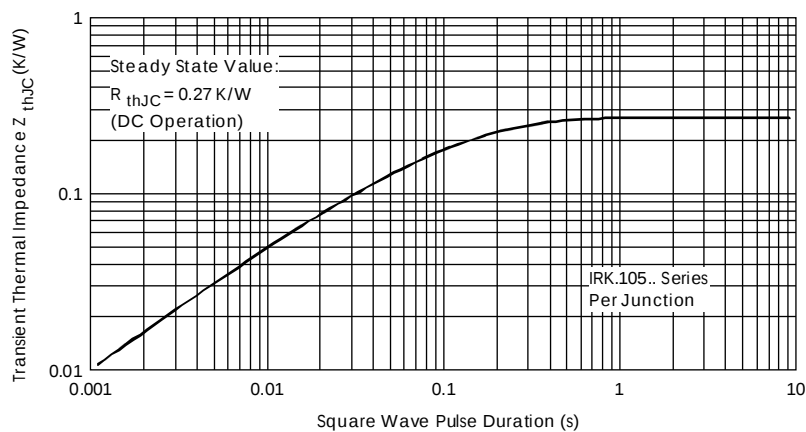


Fig. 12 - Thermal Impedance Z_{thJC} Characteristics

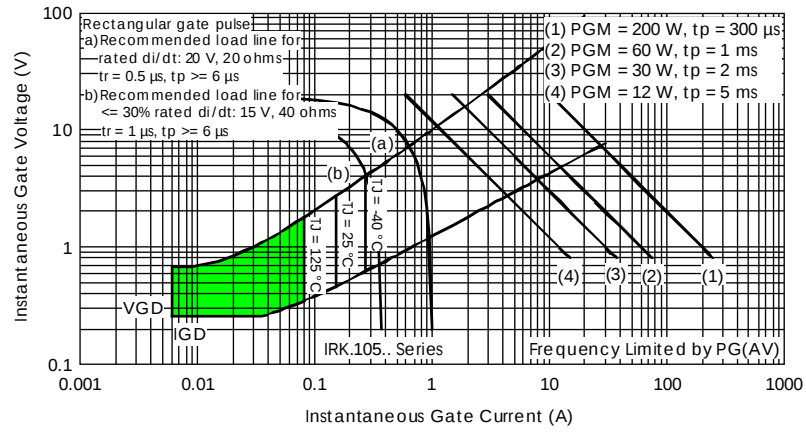


Fig. 13- Gate Characteristics